

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A semiconductor device comprising:

a semiconductor circuit which is formed inside of said semiconductor device;

[[and]]

an electrode structure which is formed on a first surface of the semiconductor device[[,]]; and

a protective film which is formed of PI (polyimide resin) on said first surface,

said electrode structure including a first electrode layer and a metal plating layer ~~which is selectively formed on said first electrode layer~~, said first electrode layer being formed of a first metal AL (aluminum) so as to have a thickness equal to or more than 0.5 μ m and connected to said semiconductor circuit, said metal plating layer being formed of a second metal on said first electrode layer by a wet electroless plating, and said second metal ~~being capable of being soldered onto an extraction electrode outside of said semiconductor device~~ including at least one of Ni (nickel) and Cu (Copper);

wherein said metal plating layer is selectively formed in a region of said first electrode layer using said protective film as a mask, and

said second metal is capable of being soldered onto an extraction electrode outside of said semiconductor device.

Claim 2 (Currently Amended): A semiconductor device according to claim 1, ~~which further comprises a protective film which is formed on said first surface,~~

~~wherein said metal plating layer is selectively formed on said first electrode layer by self-alignment using said protective film as a mask~~

wherein said semiconductor device is a MOS high power semiconductor device which further comprises a second electrode layer which is formed of a third metal on a second surface which is the opposite surface to said first surface,

said first electrode layer forms at least one of a gate electrode and a source electrode, and

said second electrode layer forms a drain electrode.

Claim 3-8 (Canceled).

Claim 9 (Currently Amended): A package for semiconductor device comprising:

a semiconductor device including a semiconductor circuit and an electrode structure, said semiconductor circuit being formed inside of said semiconductor device, said electrode structure being formed on a first surface of said semiconductor device and having a first electrode layer and a metal plating layer which is ~~selectively~~ formed on said first electrode layer,

said first electrode layer being formed of a first metal and connected to said semiconductor circuit,

said metal plating layer being formed of a second metal, said second metal being capable of being soldered onto an extraction electrode outside of said semiconductor device;

a supporting substrate which supports thereon said semiconductor device;

a lead terminal which is formed of a third metal and electrically connected to said first electrode layer; and

a metal plate which is formed of a fourth metal to serve as said extraction electrode and which connects said lead terminal to said first electrode layer via said metal plating layer.

Claim 10 (Currently Amended): A package for semiconductor device according to claim 9, which further comprises a protective film which is formed on said first surface,

wherein said metal plating layer is selectively formed ~~on~~ in a region of said first electrode layer by ~~self-alignment~~ using said protective film as a mask.

Claim 11 (Original): A package for semiconductor device according to claim 9, wherein said first metal is AL (aluminum), and said first electrode layer has a thickness of 0.5 μm or more.

Claim 12 (Original): A package for semiconductor device according to claim 9, wherein said metal plating layer is formed by a wet electroless plating.

Claim 13 (Original): A package for semiconductor device according to claim 9, wherein said second metal includes at least one of Ni (nickel) and Cu (copper).

Claim 14 (Original): A package for semiconductor device according to claim 10, wherein said protective film is formed of PI (polyimide resin).

Claim 15 (Currently Amended): A package for semiconductor device comprising:

a MOS high power semiconductor device including a semiconductor circuit and an electrode structure, said semiconductor circuit being formed inside of said semiconductor device, said electrode structure being formed on a first surface of said semiconductor device and having a first electrode layer, a metal plating layer and a second electrode layer,

said first electrode layer being formed of a first metal and connected to said semiconductor circuit, said metal plating layer being formed of a second metal ~~and selectively formed~~ on said first electrode layer, said second electrode layer being formed of a third metal on a second surface which is the opposite surface to said first surface, said second metal being capable of being soldered onto an extraction electrode outside of said semiconductor device, said first electrode layer and said metal plating layer forming at least one ~~electrode~~ of a gate electrode and a source ~~electrodes~~ electrode and said second electrode layer forming a drain electrode;

a frame plate which is formed of a fourth metal, supports said semiconductor device on said second surface of said semiconductor device and is connected to said second electrode layer;

a lead terminal which is formed of a fifth metal and is electrically connected to said first electrode layer; and

a metal plate which is formed of a sixth metal to serve as said extraction electrode and which connects said lead terminal to said first electrode layer via said metal plating layer.

Claim 16 (Currently Amended): A package for semiconductor device according to claim 15, which further comprises a protective film which is formed on said first surface,

wherein said metal plating layer is selectively formed on in a region of said first electrode layer by ~~self-alignment~~ using said protective film as a mask.

Claim 17 (Original): A package for semiconductor device according to claim 15, wherein said first metal is AL (aluminum), and said first electrode layer has a thickness of 0.5 μm or more.

Claim 18 (Original): A package for semiconductor device according to claim 15, wherein said metal plating layer is formed by a wet electroless plating.

Claim 19 (Original): A package for semiconductor device according to claim 15, wherein said second metal includes at least one of Ni (nickel) and Cu (copper).

Claim 20 (Original): A package for semiconductor device according to claim 16, wherein said protective film is formed of PI (polyimide resin).

Claim 21 (New): A package for semiconductor device according to claim 9, wherein said semiconductor device is a MOS type high power semiconductor device which further comprises a second electrode layer which is formed of a third metal on a second surface which is the opposite surface to said first surface,

said first electrode layer forms at least one of a gate electrode and a source electrode, and

said second electrode layer forms a drain electrode.